

Title (en)
HIGH DENSITY, CONTROLLED IMPEDANCE CONNECTOR

Publication
EP 0212764 A3 19890208 (EN)

Application
EP 86300288 A 19860117

Priority
US 76270685 A 19850805

Abstract (en)
[origin: EP0212764A2] A high density electrical connector is shown in which discrete dielectric wafers mount several contact elements within grooves on a first surface of the wafer while mounting a single ground plane within a recess on a second surface. This configuration, when the wafers are stacked side-by-side, forms the contacts in a stripline connection in which the impedance of each contact may be controlled. The wafers may be inserted into slots within a housing to form a high density connector for joining a daughter board to a mother board.

IPC 1-7
H01R 23/68; **H01R 13/658**

IPC 8 full level
H01R 12/04 (2006.01); **H01R 12/16** (2006.01); **H01R 13/658** (2006.01); **H01R 13/72** (2006.01)

CPC (source: EP)
H01R 12/00 (2013.01); **H01R 12/721** (2013.01); **H01R 13/6587** (2013.01)

Citation (search report)

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- [Y] US 3601753 A 19710824 - UBERBACHER EDWARD C
- [A] GB 1001569 A 19650818 - BROWN ENGINEERING COMPANY INC
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Designated contracting state (EPC)
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